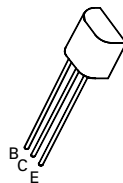


PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

FXT757

ISSUE 1 – FEB 94
FEATURES

- * 300 Volt V_{CE0}
- * 0.5 Amp continuous current
- * $P_{tot} = 1$ Watt



**E-Line
TO92 Compatible**

REFER TO ZTX757 FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.5	A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300			V	$I_C = -100\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300			V	$I_C = -10\text{mA}$, $I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$, $I_C = 0$
Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CB} = -200\text{V}$, $I_E = 0$
Emitter Cut-Off Current	I_{EBO}			-100	nA	$V_{EB} = -3\text{V}$, $I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -100\text{mA}$, $V_{CE} = -5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	40 50				$I_C = -10\text{mA}$, $V_{CE} = -5\text{V}^*$ $I_C = -100\text{mA}$, $V_{CE} = -5\text{V}^*$
Transition Frequency	f_T	30			MHz	$I_C = -10\text{mA}$, $V_{CE} = -20\text{V}$ $f = 20\text{MHz}$
Output Capacitance	C_{obo}			20	pF	$V_{CB} = -20\text{V}$, $f = 1\text{MHz}$

 *Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$